

### Description

The H8G1819M10P is a LDMOS MMIC Integrated Asymmetrical Doherty based on 2-Stage with 10W saturated output power covering frequency range from 1.805 - 1.880 GHz.

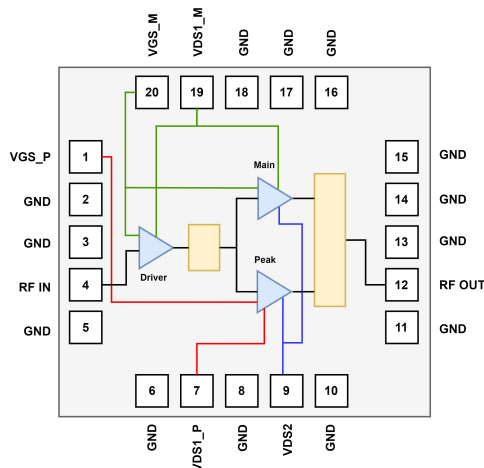
The amplifier is 50  $\Omega$  Input/Output matched with a small compact footprint 7x7 mm which makes it ideal for integration.



20 Pin LGA 7x7 mm Plastic Package



### Block Diagram



H8G1819M10P Block Diagram

### Applications

- 3GPP 5G NR FR1 n3 and 4G-LTE B3
- Power Amplifier for Small Cells
- Driver Amplifier for Micro and Macro Base Stations
- Active Antenna Array for 5G mMIMO
- Repeaters/DAS
- Mobile Infrastructure

### Features

- Operating Frequency Range: 1.805 - 1.880 GHz
- Operating Drain Voltage: +28V
- Saturation Output Power: 10W
- Power Average: 1.25W
- 50  $\Omega$  Input/Output matched
- Integrated Input Divider
- Integrated Output Combiner
- Integrated Asymmetrical Doherty Final Stage
- High Efficiency: 43.1%@1.880GHz, WCDMA
- High Gain: 27.7dB@1.880GHz, WCDMA
- Small footprint package: LGA 7x7 mm

### Ordering Information

Part Number	Description
H8G1819M10P	Reel Package
H8G1819M10PEVB	1.805 - 1.880 GHz EVB



# H8G1819M10P

## 10W, 1.805 - 1.880 GHz LDMOS MMIC Amplifier

Product datasheet

### Typical Performance

#### RF Characteristics (Pulsed CW)

Freq (GHz)	P3dB (dBm)	Gain (dB)	Eff (%)	IRL (dB)
1.805	40.0	28.3	46.6	14.7
1.880	40.2	28.3	47.0	17.0

Test conditions unless otherwise noted: 25 °C,  $V_{DD} = +28V_{dc}$ ,  $I_{DQ} = 28mA$ ,  $V_{gsp} = V_{gsm} - 0.42V$ , Pulse Width = 100us, Duty Cycle = 10% test on WATECH Application Board

#### RF Characteristics (WCDMA)

Freq (GHz)	Gain (dB)	Eff (%)	IRL (dB)	ACPR* @5MHz (dBc)	ACPR* @10MHz (dBc)
1.805	27.7	43.0	15.3	-30.1	-44.3
1.880	27.7	43.1	17.9	-30.9	-44.3

Test conditions unless otherwise noted: 25 °C,  $V_{DD} = +28V_{dc}$ ,  $I_{DQ} = 28mA$ ,  $V_{gsp} = V_{gsm} - 0.42V$ ,  $PAVG = 31 dBm$

1C-WCDMA 5MHz Signal, 7.2 dB PAR @ 0.01% CCDF test on WATECH Application Board

\*Uncorrected DPD

### Absolute Maximum Ratings

Parameter	Range/Value	Unit
Drain voltage ( $V_{DSS}$ )	-0.5 to +65	V
Gate voltage ( $V_{GS}$ )	-5 to +10	V
Drain voltage ( $V_{DD}$ )	0 to +28	V
Storage Temperature ( $T_{STG}$ )	-55 to +150	°C
Case Temperature ( $T_C$ )	-40 to +125	°C
Junction Temperature ( $T_J$ )	-40 to +175	°C

### Electrical Specification

#### DC Characteristics

Parameter	Conditions	Min	Typ	Max	Unit
Breakdown Voltage $V_{(BR)DSS}$	$V_{gs}=0V$ , $I_{ds}=100\mu A$	65	-	-	V
Gate-Source Threshold Voltage $V_{GS(th)}$	$V_{gs}=V_{ds}$ , $I_{ds}=5.2\mu A$	1.2	-	1.8	V
Drain Leakage Current $I_{DSS}$	$V_{gs}=0V$ , $V_{ds}=28V$	-	-	0.5	$\mu A$
Gate Leakage Current $I_{GSS}$	$V_{gs}=5V$ , $V_{ds}=0V$	-	-	0.05	$\mu A$

#### RF Characteristics (Pulsed CW)

Parameter	Freq (GHz)	Min	Typ.	Max	Unit
P3dB	1.880	39.5	40	-	dBm

Test conditions unless otherwise noted: 25 °C,  $V_{DD} = +28V_{dc}$ ,  $I_{DQ} = 28mA$ ,  $V_{gsp} = V_{gsm}-0.42V$ , Pulse Width = 100us, Duty Cycle = 10% test on WATECH Production Board

#### RF Characteristics (WCDMA)

Parameter	Conditions	Min	Typ.	Max	Unit
Frequency		1.880			GHz
Gain	$PAVG = 31\text{ dBm}$	25.5	27.5	30	dB
Eff	$PAVG = 31\text{ dBm}$	40	43	-	%
IRL	$PAVG = 31\text{ dBm}$	10	18	-	dB
ACPR@5MHz*	$PAVG = 31\text{ dBm}$	-	-30	-28	dBc

Test conditions unless otherwise noted: 25 °C,  $V_{DD}=+28V_{dc}$ ,  $I_{DQ} = 28mA$ ,  $V_{gsp} = V_{gsm}-0.42V$ , 1C-WCDMA 5MHz Signal, 7.2 dB PAR @ 0.01% CCDF test on WATECH Production Board

\*Uncorrected DPD

#### Load Mismatch Test

Condition	Test Result
VSWR=10:1, at all Phase Angles, $V_{DD}=+28V_{dc}$ , $I_{DQ} = 28\text{ mA}$ , $V_{gsp}=V_{gsm}-0.42V$ , $PAVG = 34\text{ dBm}$ , Frequency 1.880 GHz, test on WATECH Application Board	No Device Degradation

#### Thermal Information

Parameter	Condition	Value (Typ)	Unit
Thermal Resistance Junction to Case ( $R_{TH}$ )	$T_{CASE} = 90^{\circ}C$ , 1C-WCDMA 5MHz Signal, 7.2 dB PAR, $PAVG = 31\text{ dBm}$	11	$^{\circ}C / W$

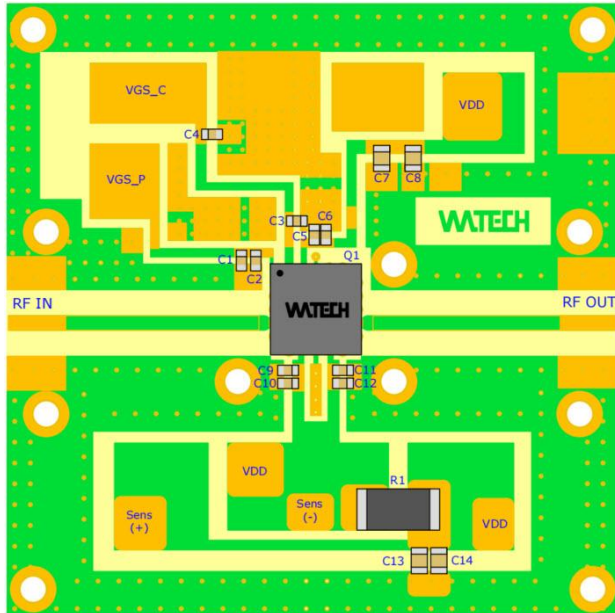


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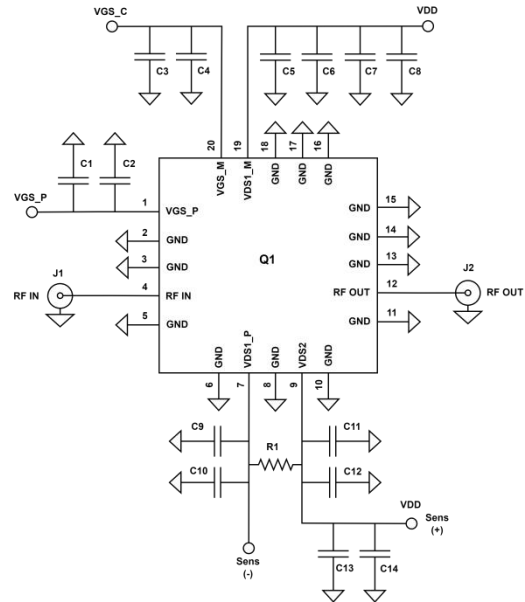
## 10W, 1.805 - 1.880 GHz LDMOS MMIC Amplifier

Product datasheet

### H8G1819M10P 1.805 - 1.880 GHz Reference Design (47 x47 mm)



EVb Layout

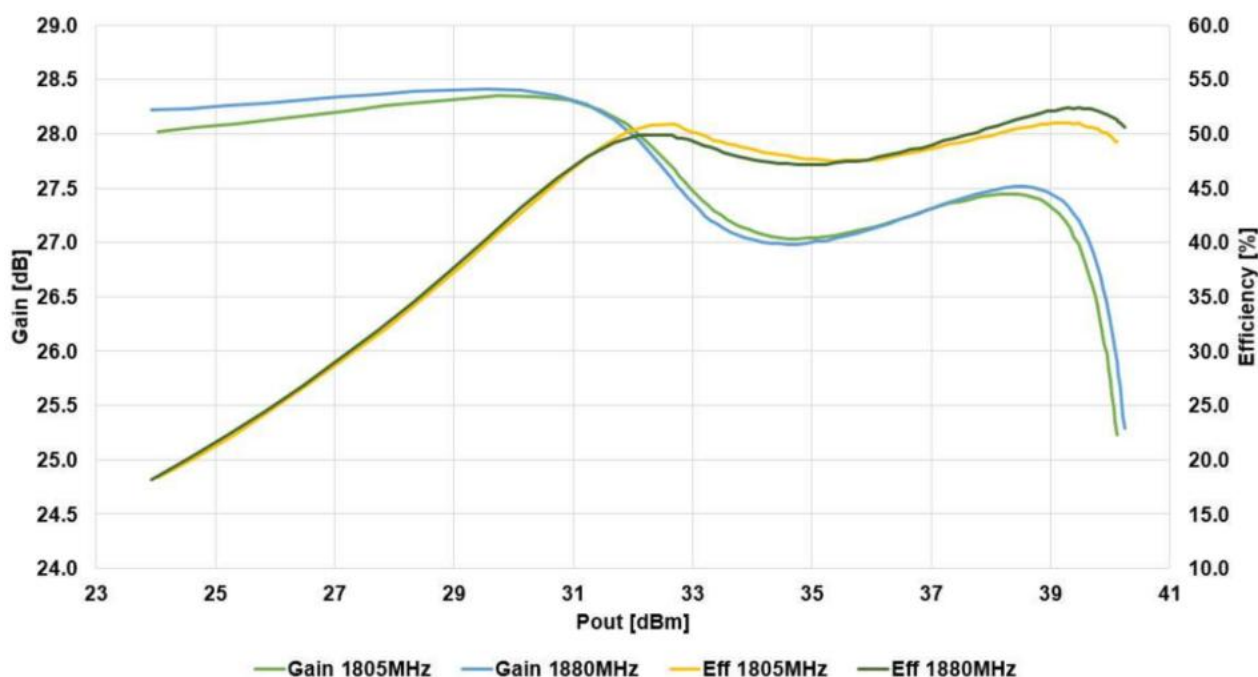


EVb Schematic

### Bill of Materials (BoM) - H8G1819M10P 1.805 - 1.880 GHz Reference Design

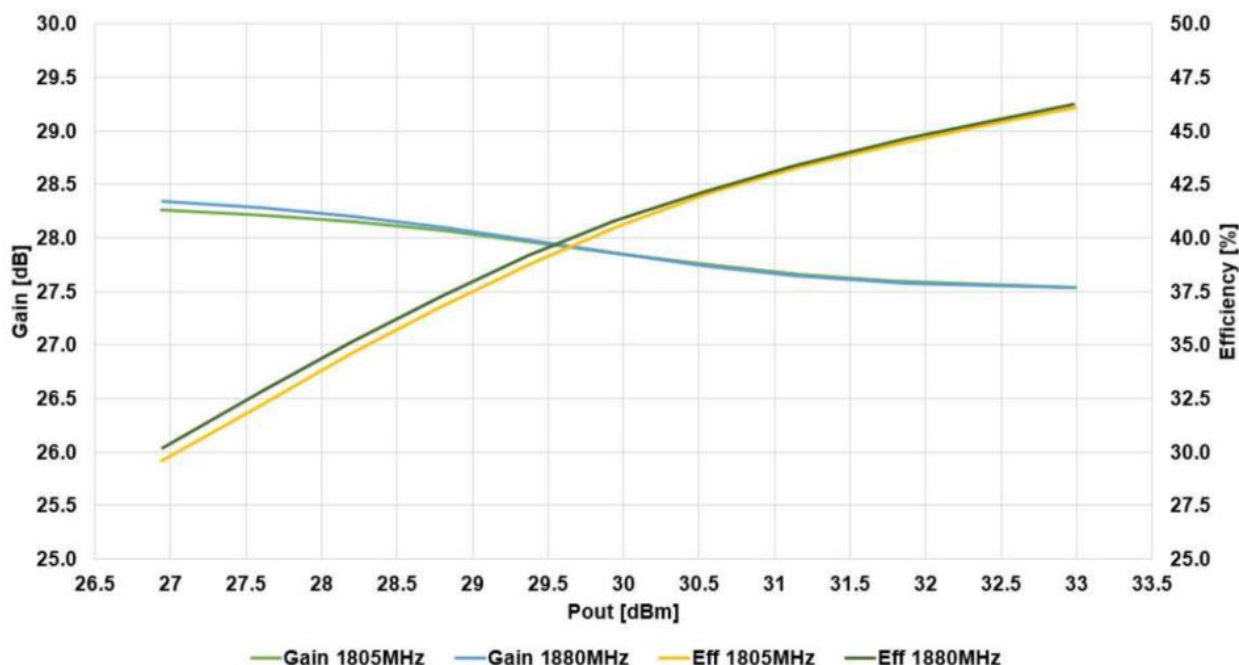
Reference	Value	Description	Manufacturer	P/N
Q1	-	10W, 1.805 - 1.880 GHz LDMOS MMIC PA	Watech	H8G1819M10P
C7,C8, C13,C14	1uF $\pm$ 10%, 0805	Multi-Layer Ceramic Capacitor	Murata	GRM219R7YA105KA12
C1-C6, C9 - C12	1uF $\pm$ 10%, 0603	Multi-Layer Ceramic Capacitor	Murata	GCM188R71E105KA64D
R1	100m $\Omega$ /1W, 0.1%	High-Precision Resistor	Vishay	Y44870R10000B0R
PCB	<ul style="list-style-type: none"><li>Rogers 4350B, er = 3.66; Thickness= 20 mil (0.508 mm); Thickness copper plating = 35 <math>\mu</math>m (1oz)</li><li>Soldered on a 47x47x10 mm Copper Base-Plate</li></ul>			

### Performance Plots



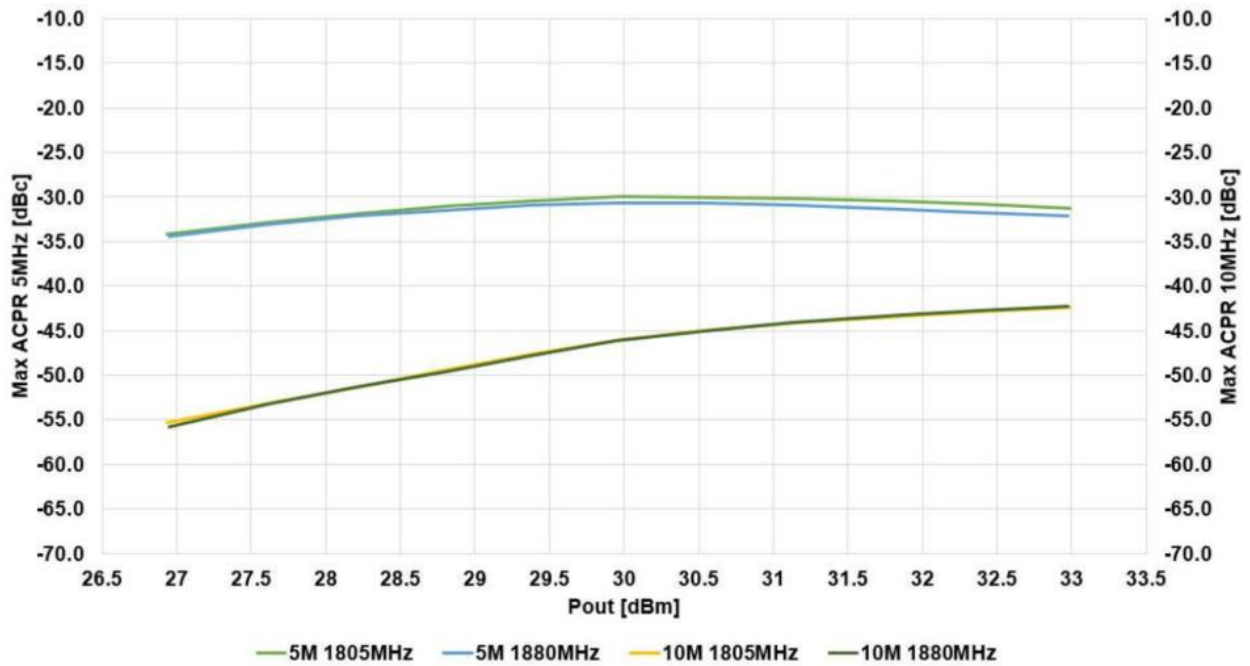
#### Pulsed CW, Gain and Efficiency vs Pout

Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ = 28mA, Vgsp = Vgsm-0.42V, Pulse Width = 100 us, Duty Cycle = 10% test on WATECH Application Board



#### WCDMA, Gain and Efficiency vs Pout

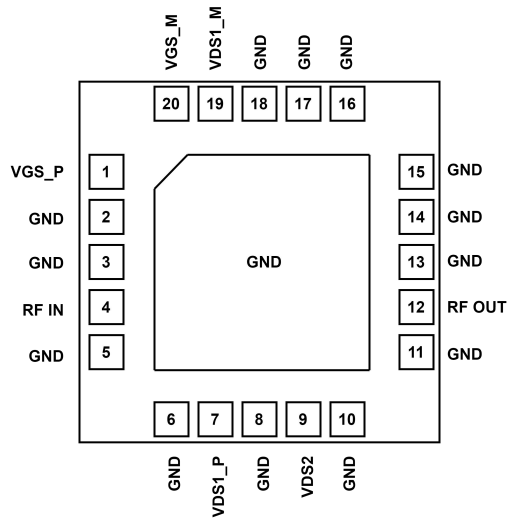
Test conditions unless otherwise noted: 25 °C, VDD = +28Vdc, IDQ = 28mA, Vgsp = Vgsm-0.42V, 1C-WCDMA 5MHz Signal, 7.2 dB PAR @ 0.01% CCDF test on WATECH Application Board



### WCDMA, ACPR\_5MHz, ACPR\_10MHz vs Pout

Test conditions unless otherwise noted: 25 °C, VDD=+28Vdc, IDQ = 28mA, Vgsp = Vgsm-0.42V, 1C-WCDMA 5MHz Signal, 7.2 dB PAR @ 0.01% CCDF test on WATECH Application Board

### Pin Configuration and Description



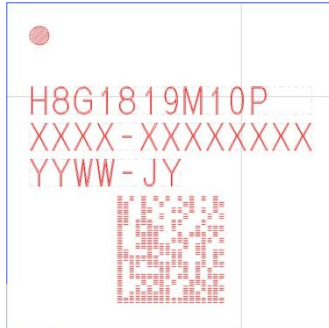
17	GND	Ground
18	GND	Ground
19	VDS1_M	Drain-Source Voltage Main Driver
20	VGS_M	Gate-Source Voltage Main

Pinout Device Configuration

Pin Number	Label	Description
1	VGS_P	Gate-Source Voltage Peak
2	GND	Ground
3	GND	Ground
4	RFIN	RF Input
5	GND	Ground
6	GND	Ground
7	VDS1_P	Drain-Source Voltage Peak Driver
8	GND	Ground
9	VDS2	Drain-Source Voltage Final Stage
10	GND	Ground
11	GND	Ground
12	RFOUT	RF Output
13	GND	Ground
14	GND	Ground
15	GND	Ground
16	GND	Ground

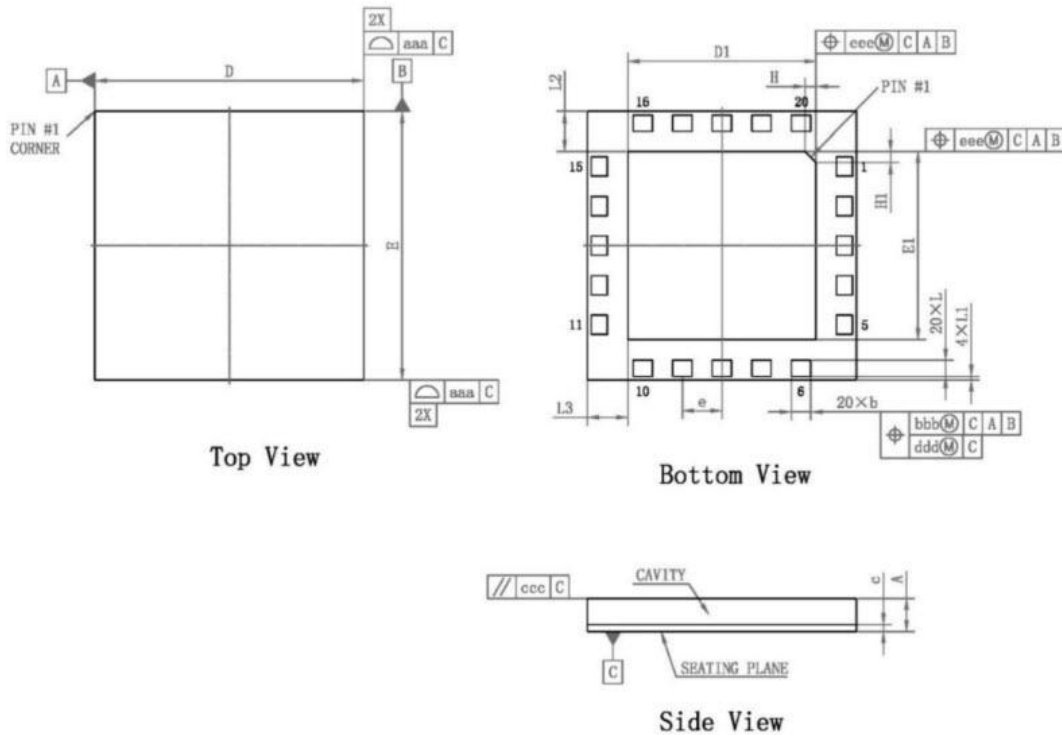


### Package Marking and Dimensions



- Line1 (fixed): Device name in W/O
- Line2 (unfixed): Marking Lot No in W/O (Sample: E596-20140001)
- Line3 (unfixed): Date Code + JY
- This Marking SPEC only stipulates the content of Marking. For marking requirements such as font and size, please refer to the latest version of "Watech Product Printing Specification"

### Marking

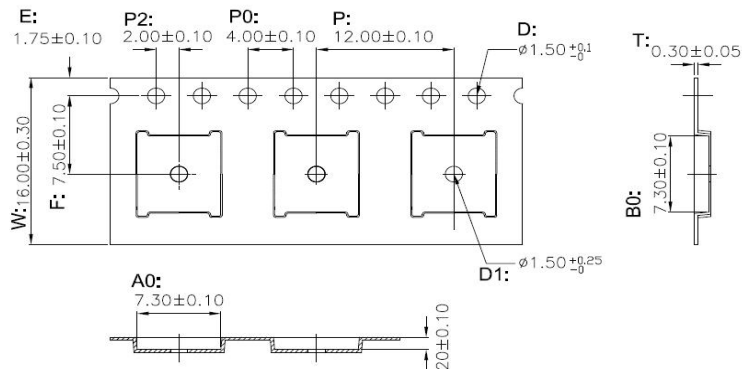


symbol	Dimension in mm			Dimension in inch		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.760	0.860	0.960	0.030	0.034	0.038
c	0.150	0.180	0.210	0.006	0.007	0.008
D	6.900	7.000	7.100	0.272	0.276	0.280
E	6.900	7.000	7.100	0.272	0.276	0.280
D1	4.800	4.900	5.000	0.189	0.193	0.197
E1	4.800	4.900	5.000	0.189	0.193	0.197
H	—	0.286	—	—	0.011	—
H1	—	0.286	—	—	0.011	—
L	0.370	0.420	0.470	0.015	0.017	0.019
L1	0.025	0.100	0.175	0.001	0.004	0.007
L2	0.975	1.050	1.125	0.038	0.041	0.044
L3	0.975	1.050	1.125	0.038	0.041	0.044
e	—	1.030	—	—	0.041	—
b	0.450	0.500	0.550	0.018	0.020	0.022
aaa	0.150			0.006		
bbb	0.150			0.006		
ccc	0.100			0.004		
ddd	0.080			0.003		
eee	0.150			0.006		

### Package Dimensions



### Tape and Reel Information



#### Notes:


1. Carrier tape color: BLACK.
2. Carrier material :PS (Polystyrene).
3. ESD surface resistivity <  $1 \times 10^{11}$   $\Omega$ /square per EJA, JEDEC TNR specification.
4. Heat deflection temperature for Tape & Reel material: 62°C
5. Vicat softening temperature (10N) for Tape & Reel material: 95°C
6. Dimension is millimeter.



Tape & Reel Packaging Descriptions

### Handling Precautions

Parameter	Grade
Moisture Sensitivity Level MSL	3

Parameter	Rating	Standard	
ESD – Human Body Model (HBM)	Class 1B	JESD22-A114	
ESD – Human Body Model (MM)	Class A	EIA/JESD22-A115	
ESD – Charged Device Model (CDM)	Class III	JESD22-C101	



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Product datasheet

### RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU.

### Datasheet Status

Document status	Product status	Definition
Objective Datasheet	Design simulation	Product objective specification
Preliminary Datasheet	Customer sample	Engineering samples and first test results
Product Datasheet	Mass production	Final product specification

### Abbreviations

Acronym	Definition
LDMOS	Laterally-Diffused Metal-Oxide Semiconductor
CW	Continuous Waveform
VSWR	Voltage Standing Wave Ratio

### Revision history

Document ID	Datasheet Status	Release Date	Revision Version
Rev 2.1	Product	May 2020	Product release
Rev 2.2	Product	March 2023	New format based on English version datasheet
Rev 2.5	Product	September 2024	Update Package and block diagram



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### Contact Information

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For the latest specifications, additional product information, worldwide sales and distribution locations and information about WATECH:

- Web: [www.watechelectronics.com](http://www.watechelectronics.com)
- Email: [MKT@huatai-elec.com](mailto:MKT@huatai-elec.com)

For technical questions and application information:

- Email: [MKT@huatai-elec.com](mailto:MKT@huatai-elec.com)

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